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Form PTO-1449

INFORMATION DISCLOSURE CITATION

Attorney Docket No. Serial No.: 10/631,948

Applicant Ayazi, et al.

(Use several sheets if necessary)

Filing Date Group 7-31-03 2834

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## INFORMATION DISCLOSURE CITATION

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Serial No.: 10/631,948

Applicant Ayazi, et al.

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mo	T	5,873,153	2-23-99	Ruby, et al.		29	25.35	8-27-96
	U	5,884,378	3-23-99	Dydyk		29	25.35	7-22-96
	V	5,894,647	4-20-99	Lakin		29	25.35	6-30-97
	W	5,914,801	6-22-99	Dhuler, et al.		359	230	9-27-96
	Х	5,976,994	11-2-99	Nguyen, et al.		438	795	6-13-97
	Y	5,998,906	12-7-99	Jerman, et al.		310	309	8-17-98
	Z	6,000,280	12-14-99	Miller, et al.		73	105	3-23-98
	a	6,051,866	4-18-00	Shaw, et al.		257	417	8-11-98
	ь	6,060,818	5-9-00	Ruby, et al.		310	363	6-2-98
	С	6,067,858	5-30-00	Clark, et al.		73	504.16	5-30-97
V	đ	6,087,747	7-11-00	Dhuler, et al.		310	90	4-1-99
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	f Bhave, et al.; Poly-Sige: A High-Q Structural Material for Integrated RF Mems; Solid-State Sensor, Actuator and Microsystems Workshop, Hilton Head Island, South Carolina, June 2-6, 2002; pp 34-37						nd	
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	h	Yasumura, et al.; Quality Fac Vol. 9, No. 1, March 2000; pp	tors in Micron- a p 117-125	and Submicron – Thick	Cantilevers; Journ	al of Micr	oelectromecha	anical Systems,
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-	1	Lifshitz, et al.; Thermoelastic Damping In Micro- and Nanomechanical Systems; Physical Review B; Vol. 61, No. 8; February 15, 2000; pp 5600-5609						
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## INFORMATION DISCLOSURE C

Attorney Docket No. Serial No.: 062020-1430 10/631,948

**Applicant** Ayazi, et al.

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	0	6,134,042	10-17-00	Dhuler, et al.		359	224	4-1-99
	p	6,215,375	4-10-01	Larson, III, et al.		333	187	3-30-99
	q	6,236,281	5-22-01	Nguyen, et al.		331	154	9-21-99
	r	6,238,946	5-29-01	Ziegler		438	50	8-17-99
	S	6,239,536	5-29-01	Lakin		310	364	9-8-98
	t	6,256,134	7-3-01	Dhuler, et al.		359	212	7-28-00
	u	6,275,122	8-14-01	Speidell, et al.		333	186	8-17-99
	v	6,275,320	8-14-01	Dhuler, et al.		359	237	9-27-99
	w	6,291,931	9-18-01	Lakin		310	364	11-23-99
4	х	6,296,779	10-2-01	Clark, et al.		216	66	2-22-99
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Attorney Docket No. 062020-1430

Serial No.: 10/631,948

**Applicant** Ayazi, et al.

(Use several sheets if necessary) Filing Date Group 7-31-03 2834 U.S. PATENT DOCUMENTS Item **Examiner** Document Date Name Class Subclass Filing Date Number **Initials** If Appropriate GG 6,348,846 2-19-02 von Gutfeld, et al. 333 201 10-14-99 HH 6,373,682 4-16-02 Goodwin-Johansson 278 361 12-15-99 II 6,377,438 Deane, et al. 4-23-02 278 361 10-23-00 IJ 6,391,674 5-21-02 Ziegler 438 **52** 12-28-00 KK 6,428,713 8-6-02 Christenson, et al. 216 10-1-99 2 LL 6,429,755 8-6-02 Speidell, et al. 333 197 1-30-01 MM 6,433,401 8-13-02 Clark, et al. 257 524 4-5-00 NN 6,480,645 11-12-02 Peale, et al. 385 18 1-30-01 00 6,485,273 11-26-02 Goodwin-Johansson 417 410.2 9-1-00 PP 6,495,892 12-17-02 Goodman, et al. 257 414 3-26-99 QQ 6,497,141 12-24-02 Turner, et al. 73 105 6-5-00 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) mo Amini, et al.; Capacitive Accelerometer; IEEE International Solid-State Circuits Conference; 2000; pp 1-3 RR Ho, et al.; Through-Support-Coupled Micromechanical Filter Array; School of Electrical and Computer Engineering; Proc. IEEE International Micro Electro Mechanical Systems Conference (MEMS'04), Maastricht, The Netherlands, Jan. 2004, pp769-772 Pourkamali, et al.; Fully Single Crystal Silicon Resonators With Deep-Submicron Dry-Etched Transducer Gaps; Proc. IEEE International Micro Electro Mechanical Systems Conference (MEMS '04), The Netherlands, Jan. 2004, pp 813-816 Pourkamali, et al.; Electrostatically Coupled Micromechanical Beam Filters; Proc. IEEE International Micro Electro Mechanical Systems Conference (MEMS '04), The Netherlands, Jan. 2004, pp. 584-587 VV Amini, et al.; A High Resolution, Stictionless, CMOS Compatible SOI Accelerometer with a Low Noise, Low Power, 0.25 µm CMOS Interface; IEEE MEMS'04, Jan. 2004, pp. 572-575 WW Humad, et al.; High Frequency Micromechanical Piezo-On-Silicon Block Resonators; IEEE; 2003

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